



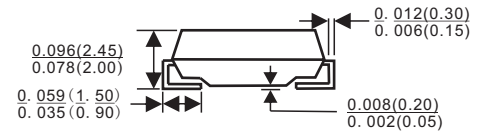
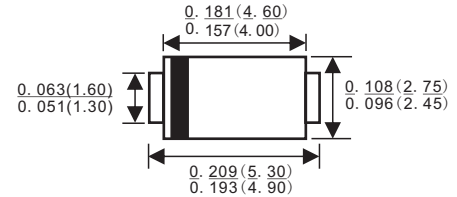
FEATURES

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Designed and qualified for industrial level

DESCRIPTION

The 10MQ100N surface mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, freewheeling diodes, battery charging, and reverse battery protection.

SMA/DO-214AC



Dimensions in inches and(millimeters)

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	DC	2.1	A
V_{RRM}		100	V
I_{FSM}	$t_p = 5 \mu s$ sine	120	A
V_F	1.5 Apk, $T_J = 125^\circ C$	0.68	V
T_J	Range	- 55 to 150	$^\circ C$

VOLTAGE RATINGS

PARAMETER	SYMBOL	10MQ100NPbF	UNITS
Maximum DC reverse voltage	V_R	100	V
Maximum working peak reverse voltage	V_{RWM}		

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current See fig. 4	$I_{F(AV)}$	50 % duty cycle at $T_L = 126^\circ C$, rectangular waveform On PC board 9 mm^2 island (0.013 mm thick copper pad area)	1.5	A
Maximum peak one cycle non-repetitive surge current, $T_J = 25^\circ C$ See fig. 6	I_{FSM}	5 μs sine or 3 μs rect. pulse	120	A
		10 ms sine or 6 ms rect. pulse	30	
Non-repetitive avalanche energy	E_{AS}	$T_J = 25^\circ C$, $I_{AS} = 0.5 \text{ A}$, $L = 8 \text{ mH}$	1.0	mJ
Repetitive avalanche current	I_{AR}		0.5	A



ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop See fig. 1	$V_{FM}^{(1)}$	1 A	$T_J = 25\text{ }^\circ\text{C}$	0.78	V
		1.5 A		0.85	
		1 A	$T_J = 125\text{ }^\circ\text{C}$	0.63	
		1.5 A		0.68	
Maximum reverse leakage current See fig. 2	$I_{RM}^{(1)}$	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_R$	0.1	mA
		$T_J = 125\text{ }^\circ\text{C}$		1	
Threshold voltage	$V_{F(TO)}$	$T_J = T_J \text{ maximum}$		0.52	V
Forward slope resistance	r_t			78.4	m Ω
Typical junction capacitance	C_T	$V_R = 10\text{ V}_{DC}$, $T_J = 25\text{ }^\circ\text{C}$, test signal = 1 MHz		38	pF
Typical series inductance	L_S	Measured lead to lead 5 mm from package body		2.0	nH
Maximum voltage rate of change	dV/dt	Rated V_R		10 000	V/ μ s

Note

(1) Pulse width < 300 μ s, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	$T_J^{(1)}$, T_{Stg}			- 55 to 150	$^\circ\text{C}$
Maximum thermal resistance, junction to ambient	R_{thJA}	DC operation		80	$^\circ\text{C/W}$
Approximate weight				0.07	g
				0.002	oz.
Marking device		Case style SMA (similar D-64)		10MQ100N	

Note

(1) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink

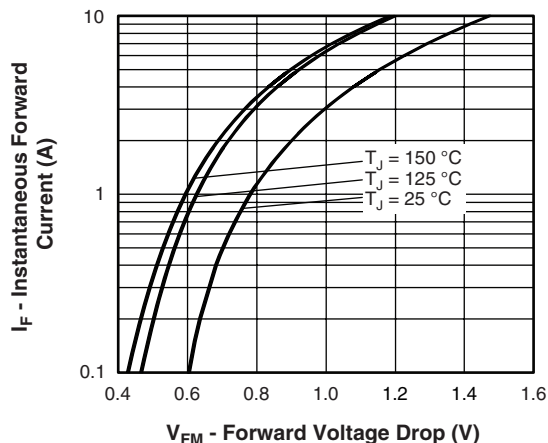
Ratings and Characteristics Curve (TA=25°C unless otherwise noted)


Fig. 1 - Maximum Forward Voltage Drop Characteristics

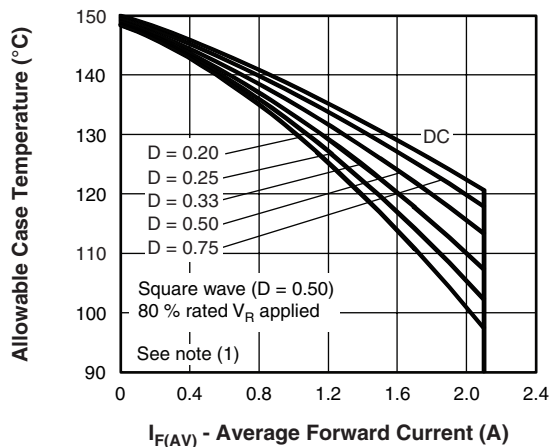


Fig. 4 - Maximum Average Forward Current vs. Allowable Lead Temperature

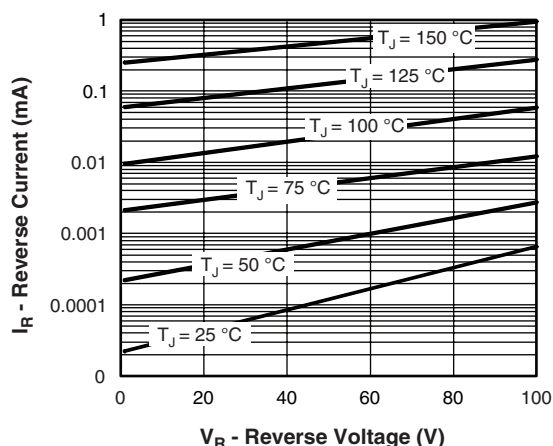


Fig. 2 - Typical Peak Reverse Current vs. Reverse Voltage

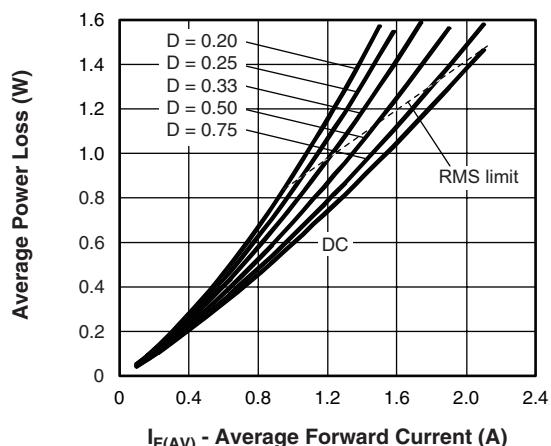


Fig. 5 - Maximum Average Forward Dissipation vs. Average Forward Current

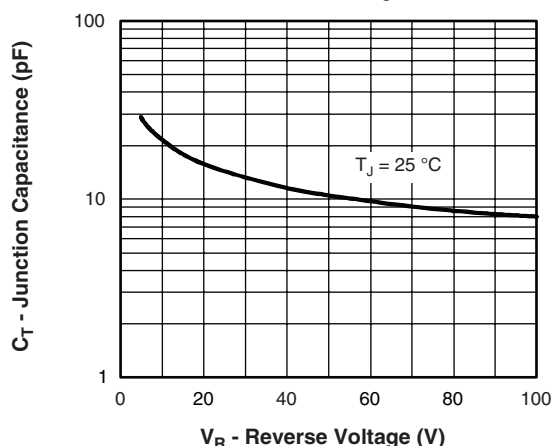


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

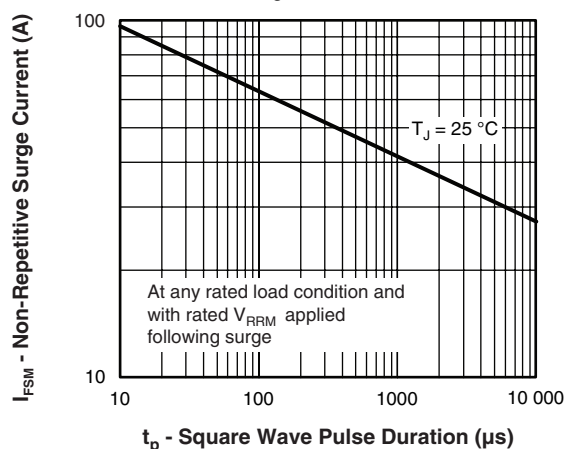


Fig. 6 - Maximum Peak Surge Forward Current vs. Pulse Duration

Note

 (1) Formula used: $T_C = T_J - (P_d + P_{dREV}) \times R_{thJC}$;

 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); P_{dREV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at $V_{R1} = 80\%$ rated V_R

PACKAGE	SPQ/PCS	CARTON SPQ/PCS	CARTON SIZE/CM	CARTON GW/KG	CARTON NW/KG
SMA	5000/REEL	80000	36X30.6X31	12.00	11.00